NPN Triple Diffused Planar Silicon Transistor

2SC4493



High-Voltage Amplifier, High-Voltage Switching Applications

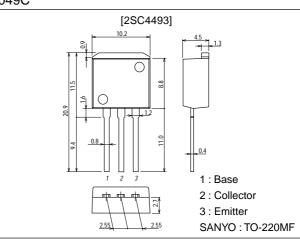
Features

- · High breakdown voltage.
- \cdot Small C_{ob}.
- \cdot High reliability (Adoption of HVP process).
- Intended for high-density mounting (Suitable for sets whose height is restricted).

Package Dimensions

unit:mm





Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		800	V
Collector-to-Emitter Voltage	VCEO		800	V
Emitter-to-Base Voltage	V _{EBO}		7	V
Collector Current	IC		20	mA
Collector Current (Pulse)	ICP		60	mA
Collector Dissipation	PC		1.65	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

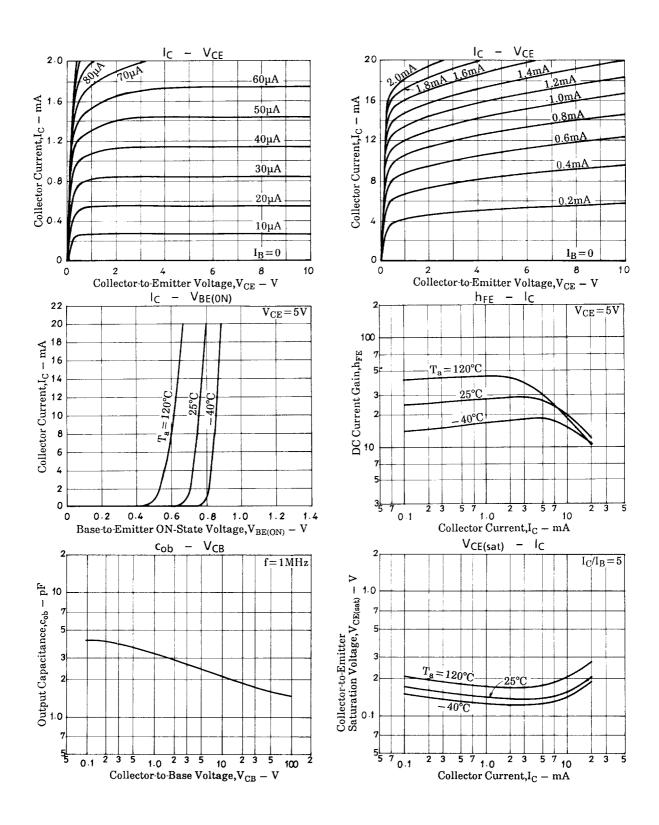
Electrical Characteristics at Ta = 25°C

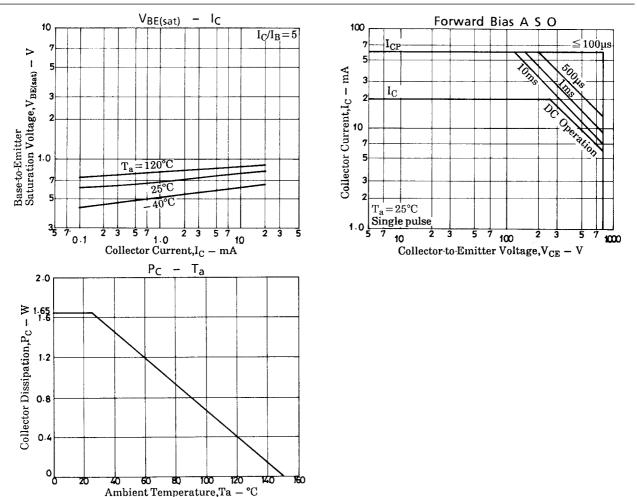
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Onit
Collector Cutoff Current	ICBO	V _{CB} =800V, I _E =0			1	μΑ
Emitter Cutoff Current	IEBO	V _{EB} =5V, I _C =0			1	μA
DC Current Gain	h _{FE} 1	V _{CE} =5V, I _C =2mA	20		50	
	h _{FE} 2	V _{CE} =5V, I _C =10mA	10			
Gain-Bandwidth Product	fT	V _{CE} =10V, I _C =2mA		40		MHz
Collector-to-Emitter Saturation Voltage	VCE(sat)	I _C =10mA, I _B =2mA			1	V
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =10mA, I _B =2mA			1.5	V

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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Onit
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =100μA, I _E =0	800			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =1mA, R _{BE} =∞	800			V
Emitter-to-Base Breakdown Voltage	V _{(BR)EBO}	I _E =100μA, I _C =0	7			V
Output Capacitance	C _{ob}	V _{CB} =100V, f=1MHz		1.6		pF





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